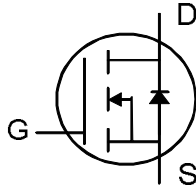


N-CHANNEL ENHANCEMENT-MODE POWER MOSFET

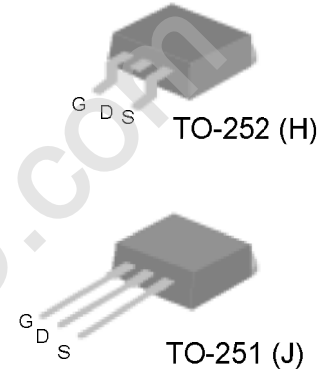
Low gate-charge
Simple drive requirement
Fast switching



BV_{DSS} 30V
 $R_{DS(ON)}$ 12m Ω
 I_D 45A

Description

The SSM60T03H is in a TO-252 package, which is widely used for commercial and industrial surface mount applications, and is well suited for low voltage applications such as DC/DC converters. The through-hole version, the SSM60T03J in TO-251, is available for low-footprint vertical mounting. These devices are manufactured with an advanced process, providing improved on-resistance and switching performance. The devices have a maximum junction temperature rating of 175°C for improved thermal margin and reliability.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	45	A
$I_D @ T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	32	A
I_{DM}	Pulsed Drain Current ¹	120	A
$P_D @ T_C=25^\circ\text{C}$	Total Power Dissipation	44	W
	Linear Derating Factor	0.352	W/ $^\circ\text{C}$
E_{AS}	Single Pulse Avalanche Energy ³	29	mJ
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Max.	Units
Rthj-c	Thermal Resistance Junction-case	3.4	$^\circ\text{C}/\text{W}$
Rthj-a	Thermal Resistance Junction-ambient	110	$^\circ\text{C}/\text{W}$

Electrical Characteristics @ $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	-	0.026	-	$\text{V}/^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=20A$	-	-	12	$\text{m}\Omega$
		$V_{GS}=4.5V, I_D=15A$	-	-	25	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
g_{fs}	Forward Transconductance ²	$V_{DS}=10V, I_D=10A$	-	25	-	S
I_{DSS}	Drain-Source Leakage Current ($T_j=25^{\circ}\text{C}$)	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
	Drain-Source Leakage Current ($T_j=175^{\circ}\text{C}$)	$V_{DS}=24V, V_{GS}=0V$	-	-	250	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 20V$	-	-	± 100	nA
Q_g	Total Gate Charge ²	$I_D=20A$	-	11.6	-	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=24V$	-	3.9	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	7	-	nC
$t_{d(on)}$	Turn-on Delay Time ²	$V_{DS}=15V$	-	8.8	-	ns
t_r	Rise Time	$I_D=20A$	-	57.5	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	18.5	-	ns
t_f	Fall Time	$R_D=0.75\Omega$	-	6.4	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	1135	-	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	200	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	135	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=45A, V_{GS}=0V$	-	-	1.3	V
t_{rr}	Reverse Recovery Time	$I_S=20A, V_{GS}=0V,$	-	23.3	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	16	-	nC

Notes:

1. Pulse width limited by safe operating area.
2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. $V_{DD}=25V$, $L=100\mu H$, $R_G=25\Omega$, $I_{AS}=24A$.

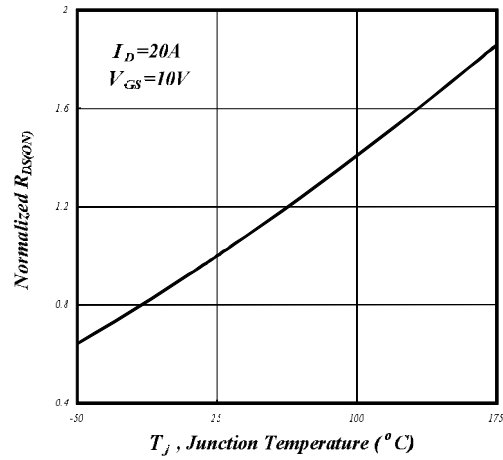
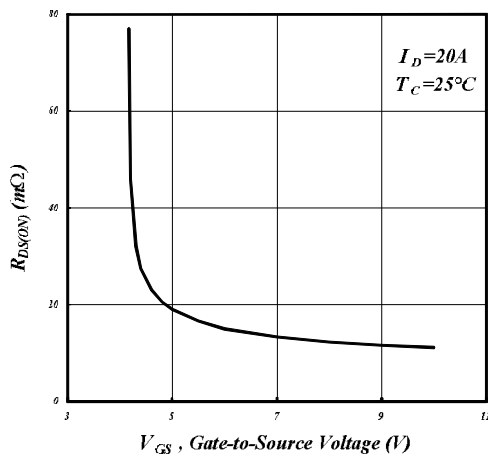
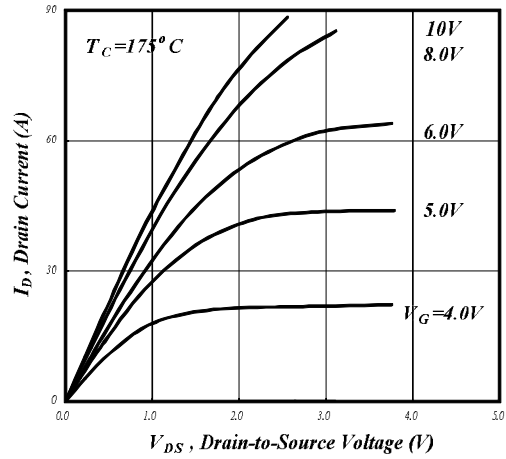
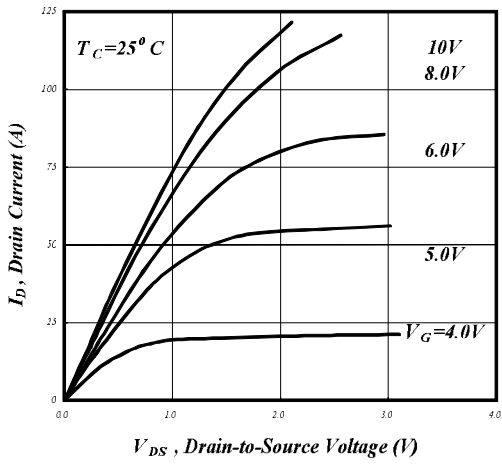


Fig 3. On-Resistance vs. Gate Voltage

Fig 4. Normalized On-Resistance vs. Junction Temperature

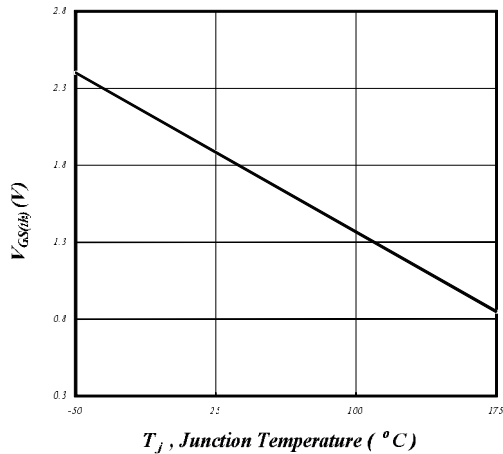
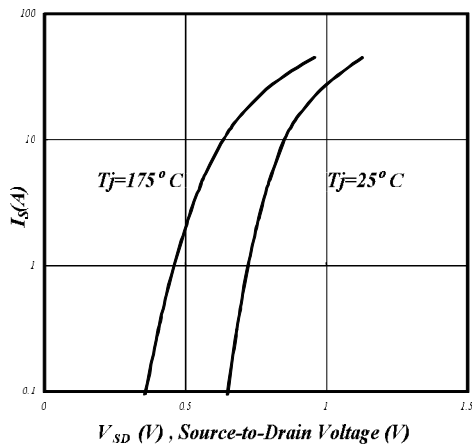


Fig 5. Forward Characteristic of Reverse Diode

Fig 6. Gate Threshold Voltage vs. Junction Temperature

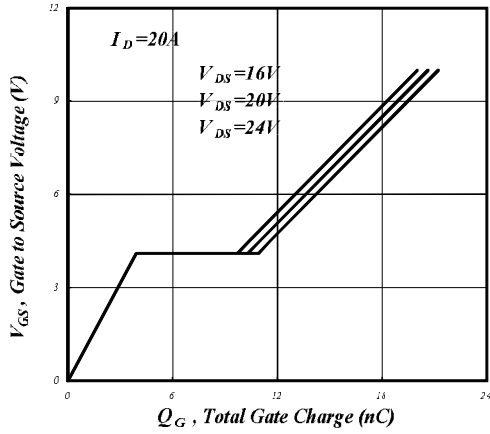


Fig 7. Gate Charge Characteristics

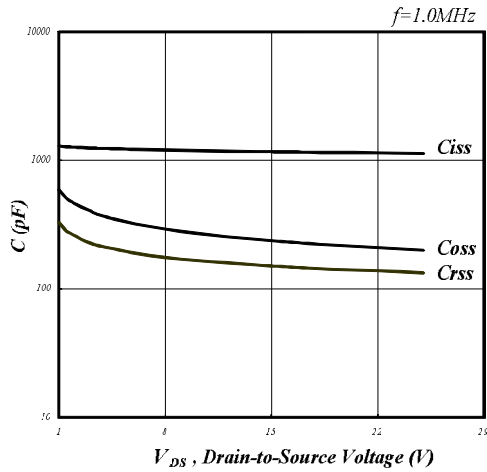


Fig 8. Typical Capacitance Characteristics

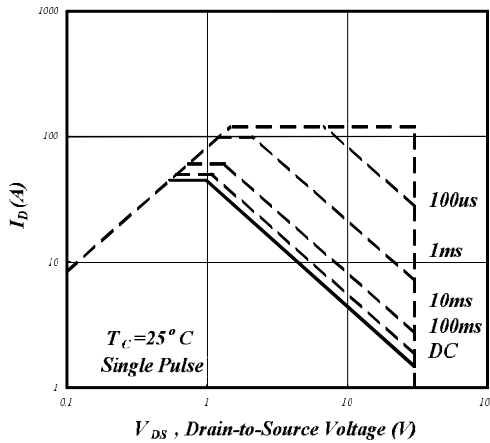


Fig 9. Maximum Safe Operating Area

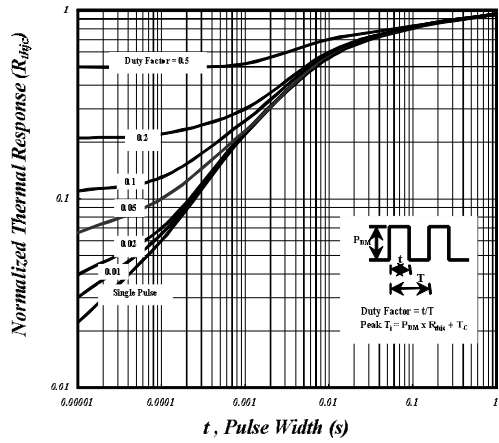


Fig 10. Effective Transient Thermal Impedance

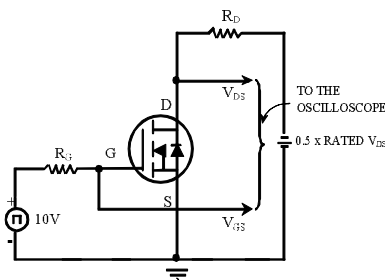


Fig 11. Switching Time Circuit

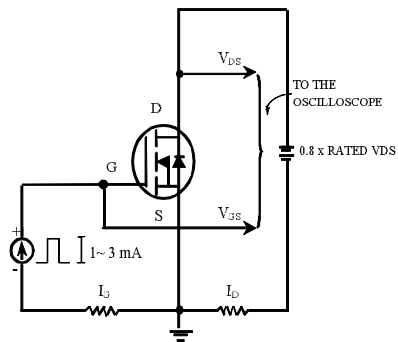


Fig 12. Gate Charge Circuit

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